ABSTRACT OF THE DISCLOSURE

In a liquid phase growth process comprising immersing a substrate in a melt held in a crucible, a crystal material having been dissolved in the melt, and growing a crystal on the substrate, at least a group of substrates to be immersed in the melt held in the crucible are fitted to the supporting rack at a position set aside from the center of rotation of the crucible or supporting rack, and the crystal is grown on the surface of the substrate thus disposed. This can provide a liquid phase growth process which can attain a high growth rate, can enjoy uniform distribution of growth rate in each substrate and between the substrates even when substrates are set in a large number in one batch, and can readily keep the melt from reaction and contamination even when the system has a large size, and provide a liquid phase growth system suited for carrying out the process.